

MAC12HCD, MAC12HCM, MAC12HCN

Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full-wave, silicon gate-controlled devices are needed.

Features

- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 80°C
- High Surge Current Capability – 100 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|--|-------------------|--------------------|
| Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) | V _{DRM} , V _{RRM} | 400 600 800 | V |
| On-State RMS Current (All Conduction Angles; T _C = 80°C) | I _{T(RMS)} | 12 | A |
| Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _J = 125°C) | I _{TSM} | 100 | A |
| Circuit Fusing Consideration (t = 8.33 ms) | I ² t | 41 | A ² sec |
| Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C) | P _{GM} | 16 | W |
| Average Gate Power (t = 8.3 ms, T _C = 80°C) | P _{G(AV)} | 0.35 | W |
| Operating Junction Temperature Range | T _J | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

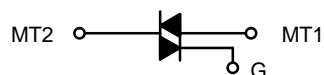
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



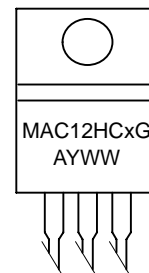
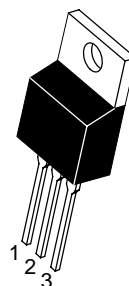
ON Semiconductor®

<http://onsemi.com>

TRIACS 12 AMPERES RMS 400 thru 800 VOLTS



MARKING DIAGRAM



TO-220AB
CASE 221A-09
STYLE 4

- x = D, M, or N
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

PIN ASSIGNMENT

| | |
|---|-----------------|
| 1 | Main Terminal 1 |
| 2 | Main Terminal 2 |
| 3 | Gate |
| 4 | Main Terminal 2 |

ORDERING INFORMATION

| Device | Package | Shipping |
|-----------|-----------------------|-----------------|
| MAC12HCD | TO-220AB | 50 Units / Rail |
| MAC12HCDG | TO-220AB (Pb-Free) | 50 Units / Rail |
| MAC12HCM | TO-220AB | 50 Units / Rail |
| MAC12HCMG | TO-220AB (Pb-Free) | 50 Units / Rail |
| MAC12HCN | TO-220AB | 50 Units / Rail |
| MAC12HCNG | TO-220AB (Pb-Free) | 50 Units / Rail |

Preferred devices are recommended choices for future use and best overall value.

MAC12HCD, MAC12HCM, MAC12HCN

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------|---------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.2 | $^{\circ}C/W$ |
| Junction-to-Ambient | $R_{\theta JA}$ | 62.5 | |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | T_L | 260 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|---|--------------------|---|---|------|----|
| Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}, \text{ Gate Open}$) | I_{DRM}, I_{RRM} | - | - | 0.01 | mA |
| $T_J = 25^{\circ}C$ | | - | - | 2.0 | |
| $T_J = 125^{\circ}C$ | | - | - | | |

ON CHARACTERISTICS

| | | | | | |
|---|----------|-----|---|------|----|
| Peak On-State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A}$) | V_{TM} | - | - | 1.85 | V |
| Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$) | I_{GT} | | | | mA |
| MT2(+), G(+) | | 10 | - | 50 | |
| MT2(+), G(-) | | 10 | - | 50 | |
| MT2(-), G(-) | | 10 | - | 50 | |
| Holding Current ($V_D = 12 \text{ V}, \text{ Gate Open}, \text{ Initiating Current} = \pm 150 \text{ mA}$) | I_H | - | - | 60 | mA |
| Latch Current ($V_D = 12 \text{ V}, I_G = 50 \text{ mA}$) | I_L | | | | mA |
| MT2(+), G(+) | | - | - | 60 | |
| MT2(+), G(-) | | - | - | 80 | |
| MT2(-), G(-) | | - | - | 60 | |
| Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$) | V_{GT} | | | | V |
| MT2(+), G(+) | | 0.5 | - | 1.5 | |
| MT2(+), G(-) | | 0.5 | - | 1.5 | |
| MT2(-), G(-) | | 0.5 | - | 1.5 | |

DYNAMIC CHARACTERISTICS

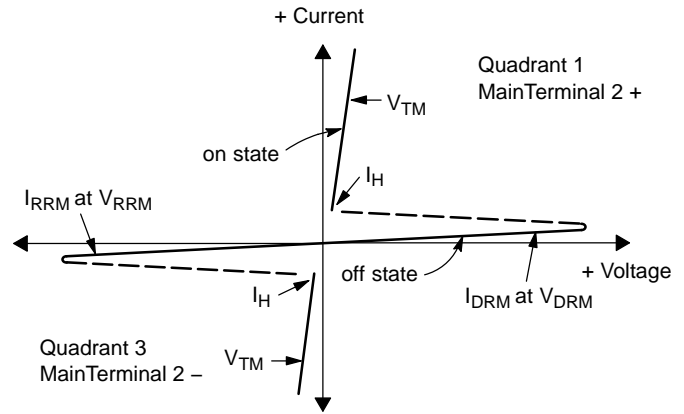
| | | | | | |
|---|-------------|-----|---|----|------------------|
| Rate of Change of Commutating Current ($V_D = 400 \text{ V}, I_{TM} = 4.4 \text{ A}, \text{ Commutating } dv/dt = 18 \text{ V}/\mu\text{s}, \text{ Gate Open}, T_J = 125^{\circ}C, f = 250 \text{ Hz}, C_L = 10 \mu\text{F}, L_L = 40 \text{ mH}, \text{ with Snubber}$) | $(di/dt)_c$ | 15 | - | - | A/ms |
| Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}, \text{ Exponential Waveform}, \text{ Gate Open}, T_J = 125^{\circ}C$) | dv/dt | 600 | - | - | V/ μs |
| Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 μsec ; diG/dt = 200 mA/ μsec ; f = 60 Hz | di/dt | - | - | 10 | A/ μs |

2. Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

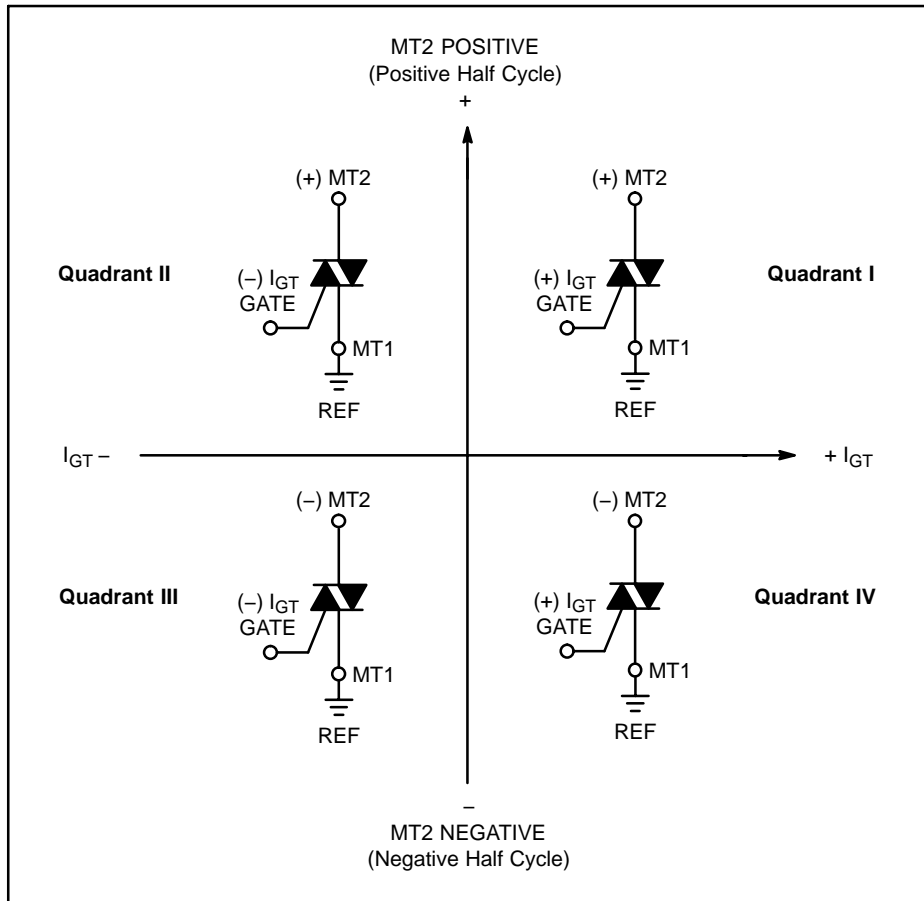
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Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|-----------|---|
| V_{DRM} | Peak Repetitive Forward Off State Voltage |
| I_{DRM} | Peak Forward Blocking Current |
| V_{RRM} | Peak Repetitive Reverse Off State Voltage |
| I_{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Maximum On State Voltage |
| I_H | Holding Current |



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used.

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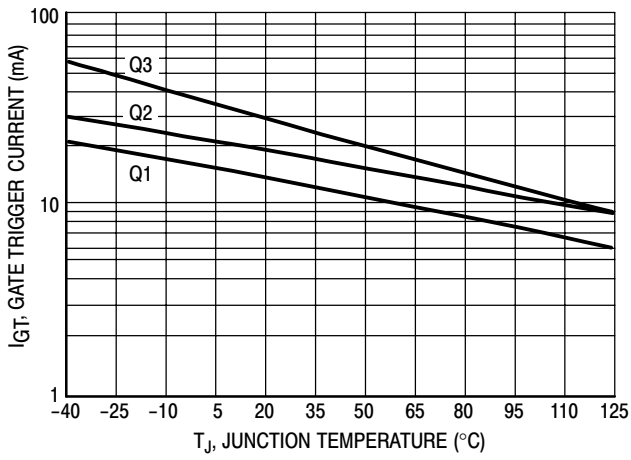


Figure 1. Typical Gate Trigger Current versus Junction Temperature

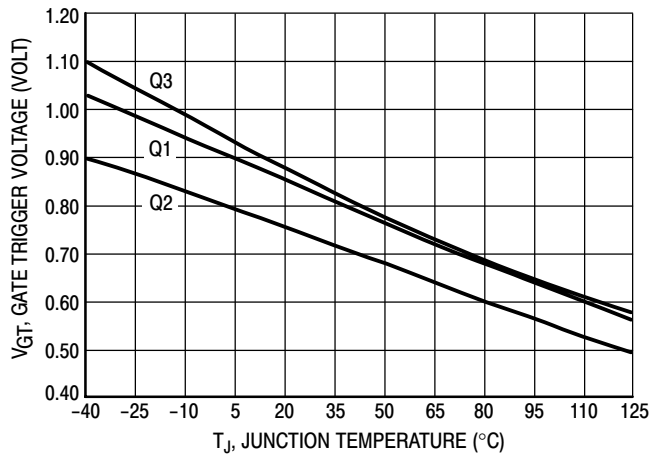


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

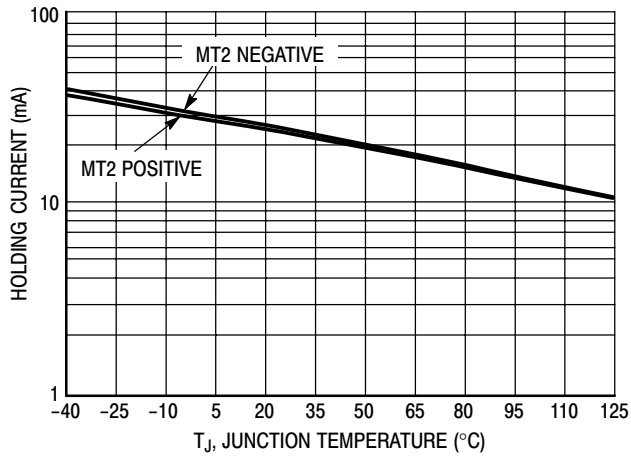


Figure 3. Typical Holding Current versus Junction Temperature

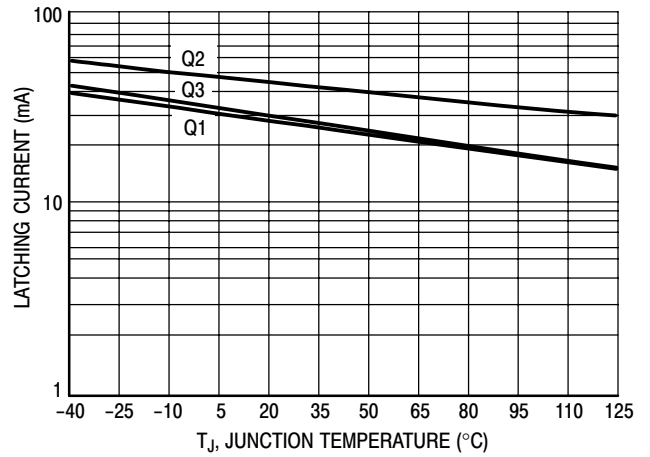


Figure 4. Typical Latching Current versus Junction Temperature

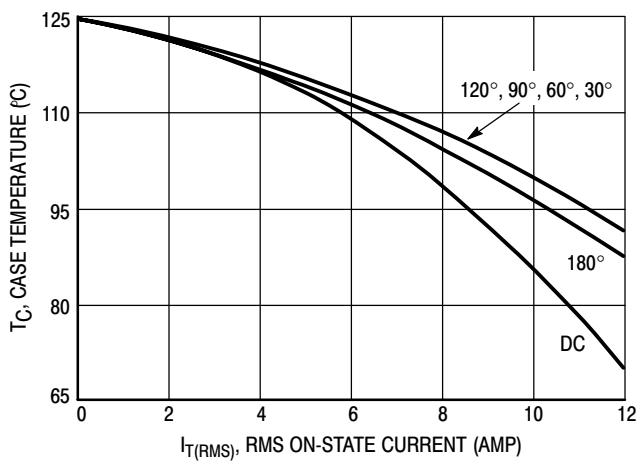


Figure 5. Typical RMS Current Derating

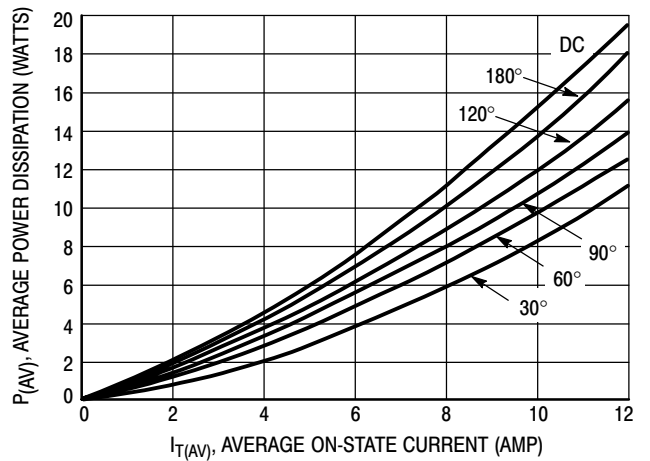


Figure 6. On-State Power Dissipation

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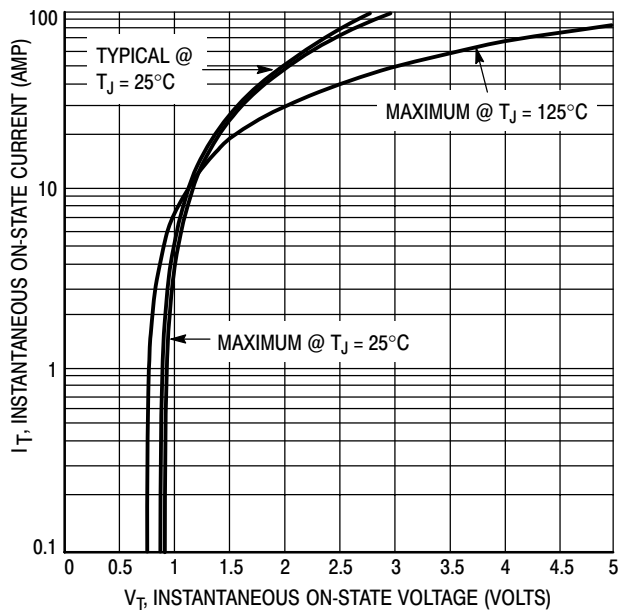


Figure 7. Typical On-State Characteristics

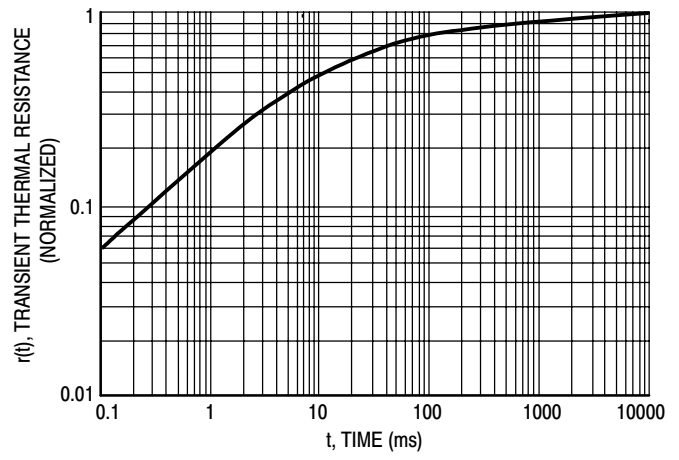
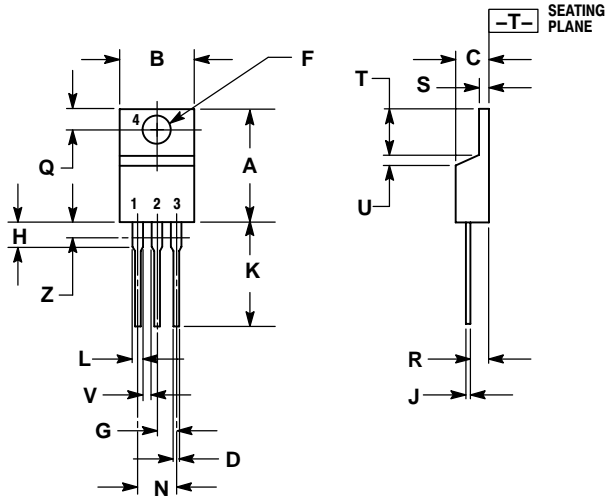


Figure 8. Typical Thermal Response

MAC12HCD, MAC12HCM, MAC12HCN

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-09
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

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